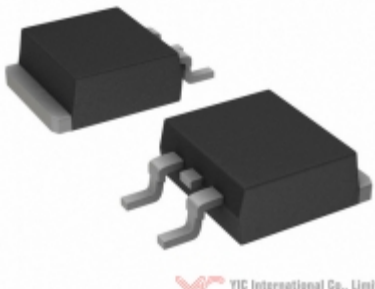


	FQB4N20LTM	
	Hersteller-Teilenummer:	FQB4N20LTM
	Hersteller / Marke:	AMI Semiconductor / ON Semiconductor
	Teil der Beschreibung:	MOSFET N-CH 200V 3.8A D2PAK
	Datenblätter:	 FQB4N20LTM.pdf
	RoHS Status:	Bleifrei / RoHS-konform
<p>Image may be representation. See specs for product details.</p>	Lagerzustand:	New original, 32363 pcs Stock Available.
	Liefern von:	Hong Kong
	Versandweg:	DHL/Fedex/TNT/UPS/EMS

Spezifikationen

Teilenummer	FQB4N20LTM
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 200V 3.8A D2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	32363 pcs Stock
detaillierte Beschreibung	N-Channel 200V 3.8A (Tc) 3.13W (Ta), 45W (Tc)
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D ² PAK (TO-263AB)
Verlustleistung (max)	3.13W (Ta), 45W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	200V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	3.8A (Tc)
Rds On (Max) @ Id, Vgs	1.35 Ohm @ 1.9A, 10V
VGS (th) (Max) @ Id	2V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	5.2nC @ 5V
Eingabekapazität (Ciss) (Max) @ Vds	310pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	5V, 10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)









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Sie können auch interessiert sein:

 <p>FQB4N25TM Fairchild/ON Semiconductor MOSFET N-CH 250V 3.6A D2PAK</p>	 <p>FQB4N20L VB FQB4N20L VB</p>	 <p>FQB47P06TM FAIRCHI FQB47P06TM FAIRCHI</p>	 <p>FQB4N20LTM Fairchild/ON Semiconductor MOSFET N-CH 200V 3.8A D2PAK</p>
 <p>FQB4N20 VB FQB4N20 VB</p>	 <p>FQB4N20TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 200V 3.6A D2PAK</p>	 <p>FQB4N25TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 250V 3.6A D2PAK</p>	 <p>FQB4N20TM Fairchild/ON Semiconductor MOSFET N-CH 200V 3.6A D2PAK</p>

heiße Teile

Mehr

 FQB34P10TM	 FQB34P10TM_F085	 FQB3N25TM	 FQB3N25TM	 FQB3N30TM
 FQB3N30TM	 FQB3N40TM	 FQB3N40TM	 FQB3N60C	 FQB3N80TM
 FQB3N80TM	 FQB3N90TM	 FQB3N90TM	 FQB3P20TM	 FQB3P20TM
 FQB3P50TM	 FQB3P50TM	 FQB44N10	 FQB44N10TM	 FQB44N10TM
 FQB46N15	 FQB46N15TM	 FQB47P06	 FQB47P06TM	 FQB4N20L
 FQB4N20LTM	 FQB4N20TM	 FQB4N20TM	 FQB4N25TM	 FQB4N25TM
 FQB4N20TM	 FQB4N50TM	 FQB4N50TM	 FQB4N60C	 FQB4N80TM
 FQB4N80TM	 FQB4N90TM	 FQB4N90TM	 FQB4P25TM	 FQB4P25TM
 FQB50N03	 FQB50N06	 FQB50N06C	 FQB50N06L	 FQB50N06LTM
 FQB50N06LTM	 FQB50N06M	 FQB50N06TM	 FQB50N06TM	 FQB50N06TM-NL

Contact us: Info@Y-IC.com

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